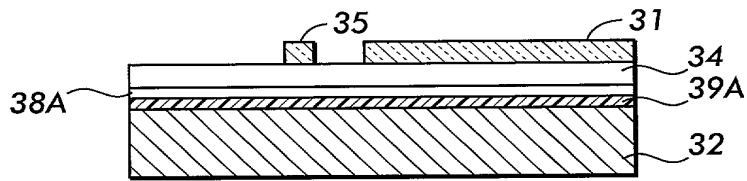
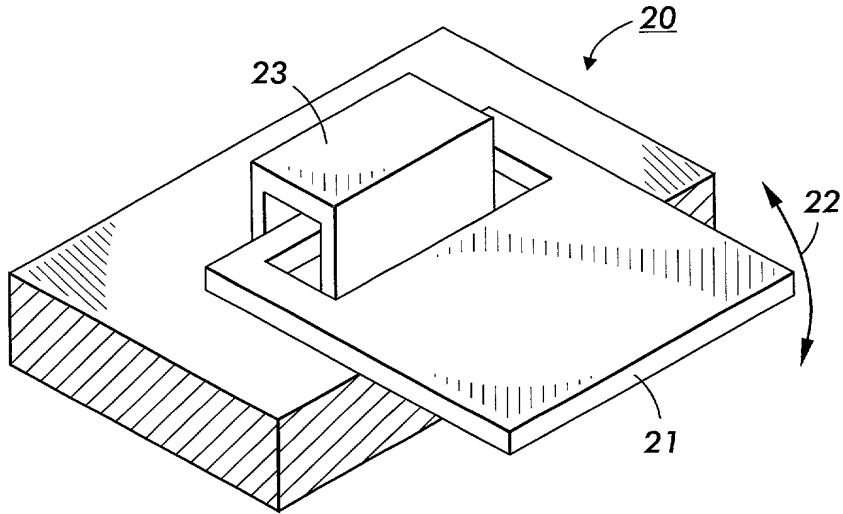


A cross-sectional view of a semiconductor device. It shows a large rectangular block labeled 'Si WAFER' with reference numeral 11. On top of the wafer, there is a thin layer labeled 10, and above that, a thicker layer labeled 15. The layers 10 and 15 are shown as a single unit with a hatched pattern.

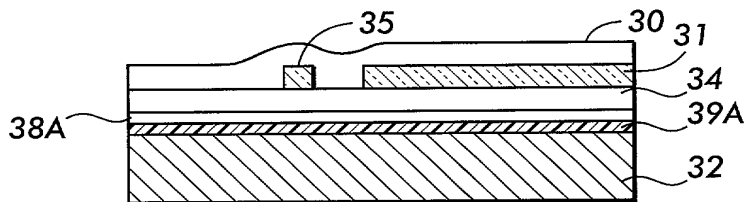
A cross-sectional view of a semiconductor device. It shows a substrate 11 at the bottom. On top of the substrate is a thin layer 10. Above layer 10 is a patterned layer 12, which has a gap 15 in its center.

A cross-sectional view of a semiconductor device. It shows a substrate 11 at the bottom. Above the substrate is a thin layer 12. Above layer 12 is a thin layer 14. Above layer 14 is a thin layer 10. Above layer 10 is a thin layer 15. The layers 12, 14, 10, and 15 are shown with different hatching patterns to distinguish them.

**FIG. 2**

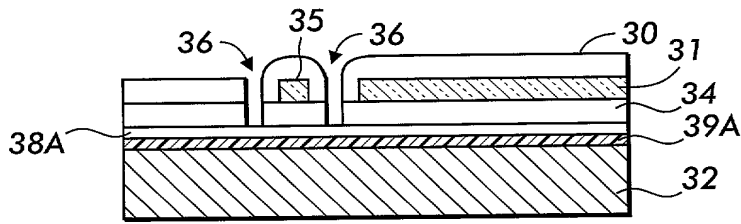


**FIG. 3**  
PRIOR ART

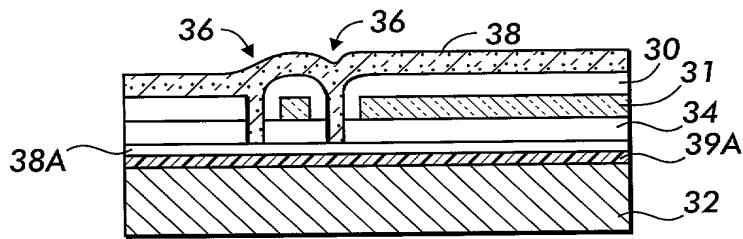


**FIG. 4**  
PRIOR ART

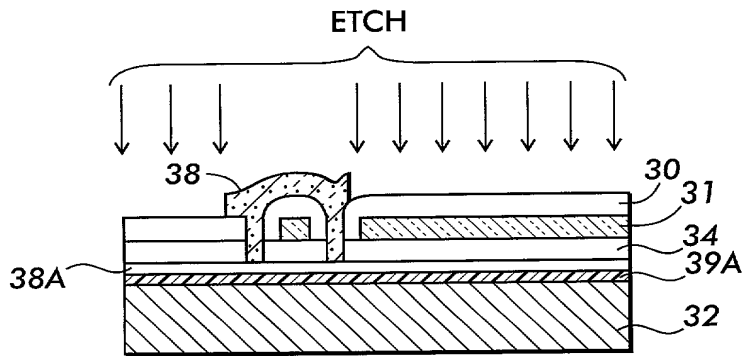
2020102690400F



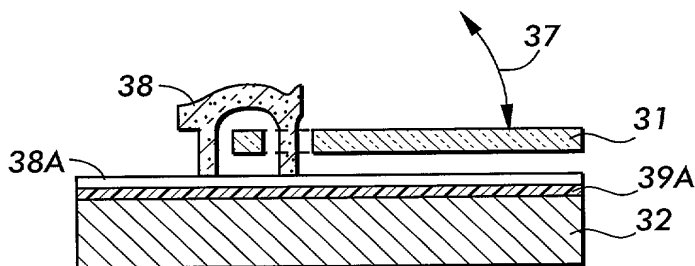
**FIG. 5**  
PRIOR ART



**FIG. 6**  
PRIOR ART



**FIG. 7**  
PRIOR ART



**FIG. 8**  
PRIOR ART

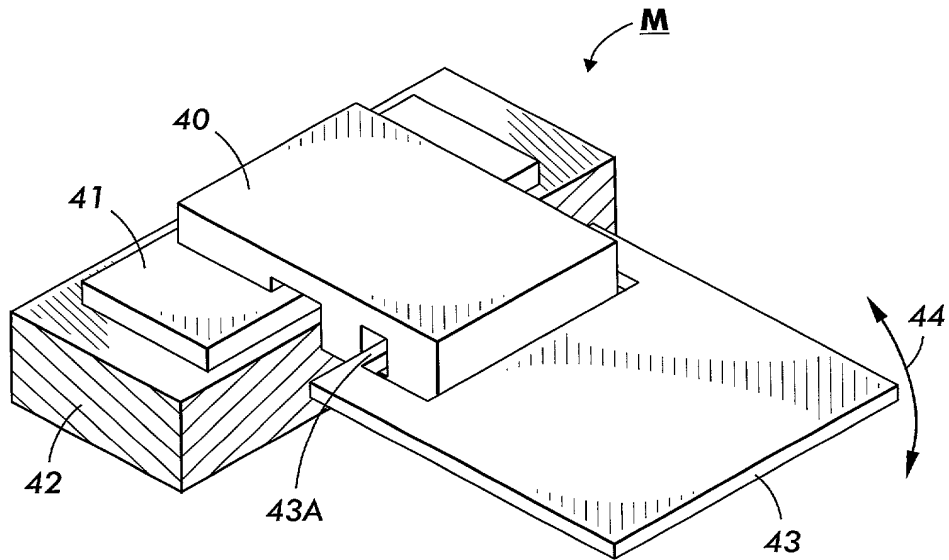


FIG. 9

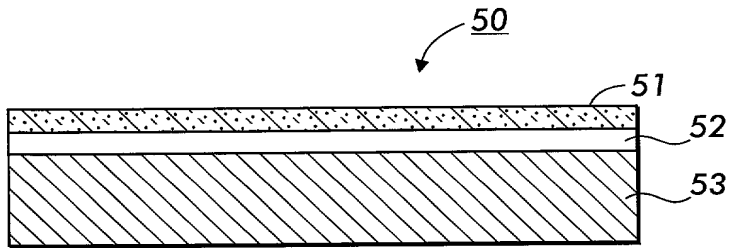


FIG. 10

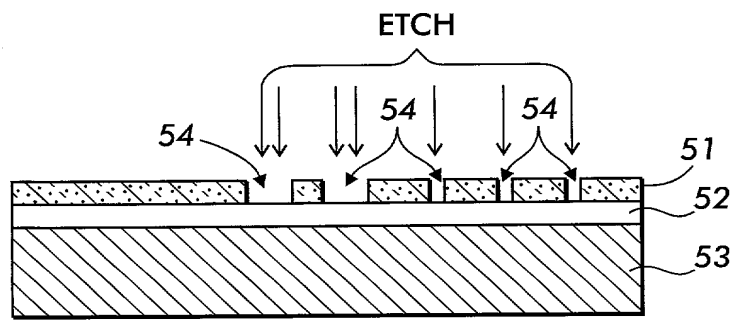


FIG. 11

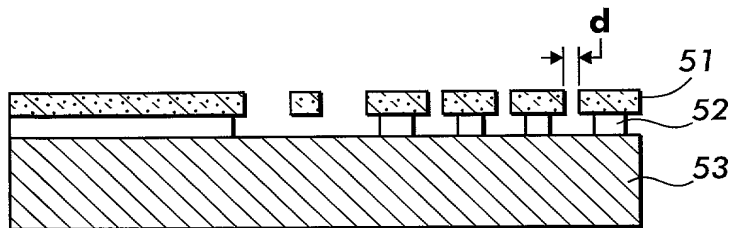


FIG. 12

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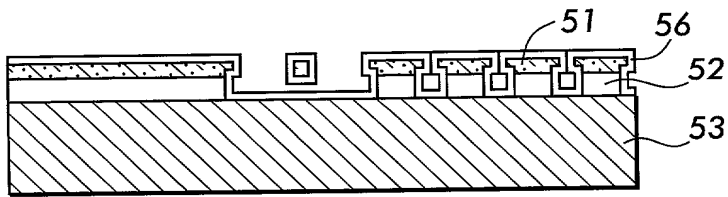


FIG. 13A

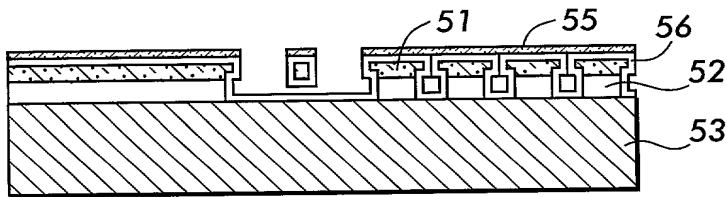


FIG. 13B

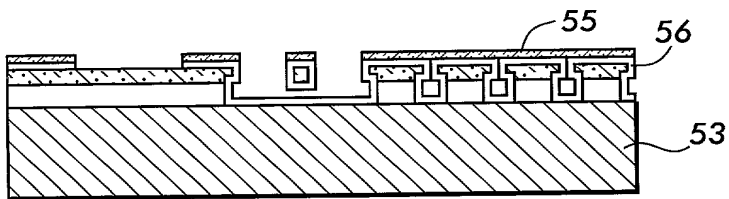


FIG. 14

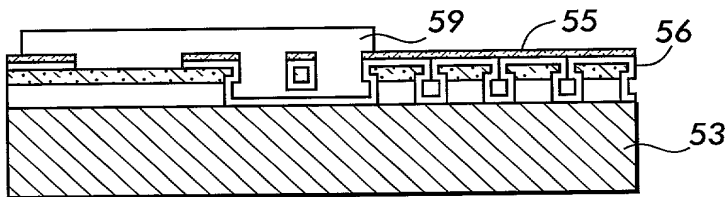


FIG. 15

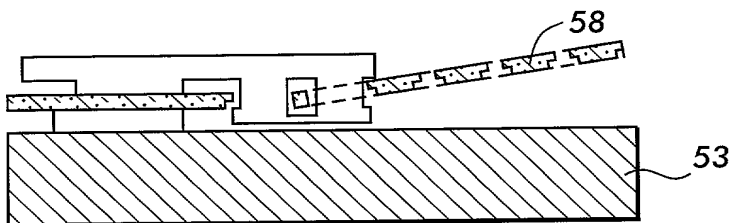


FIG. 16

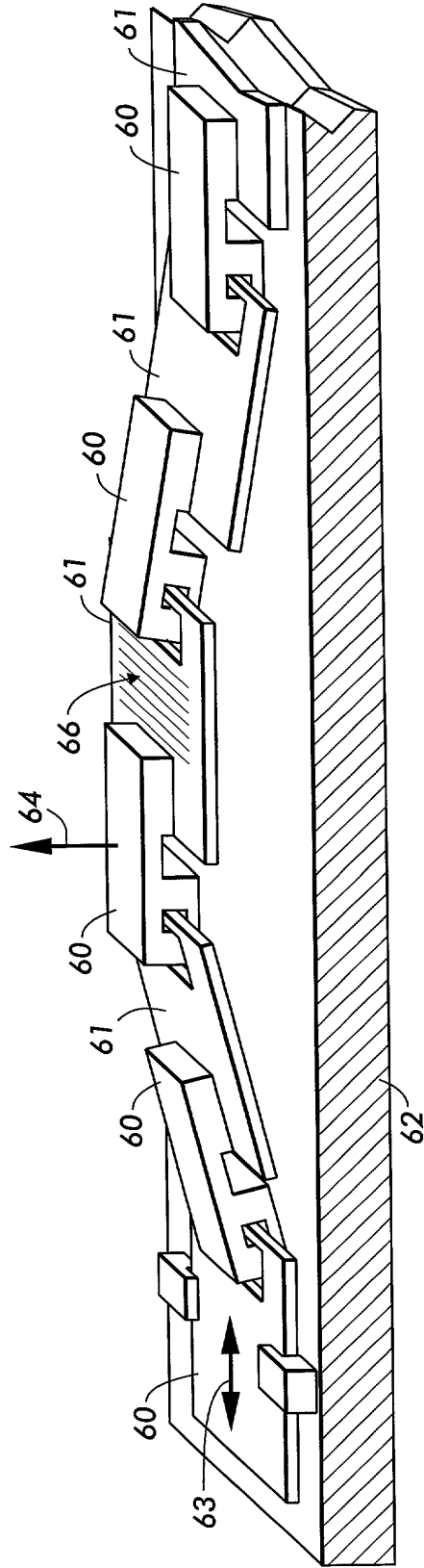


FIG. 17

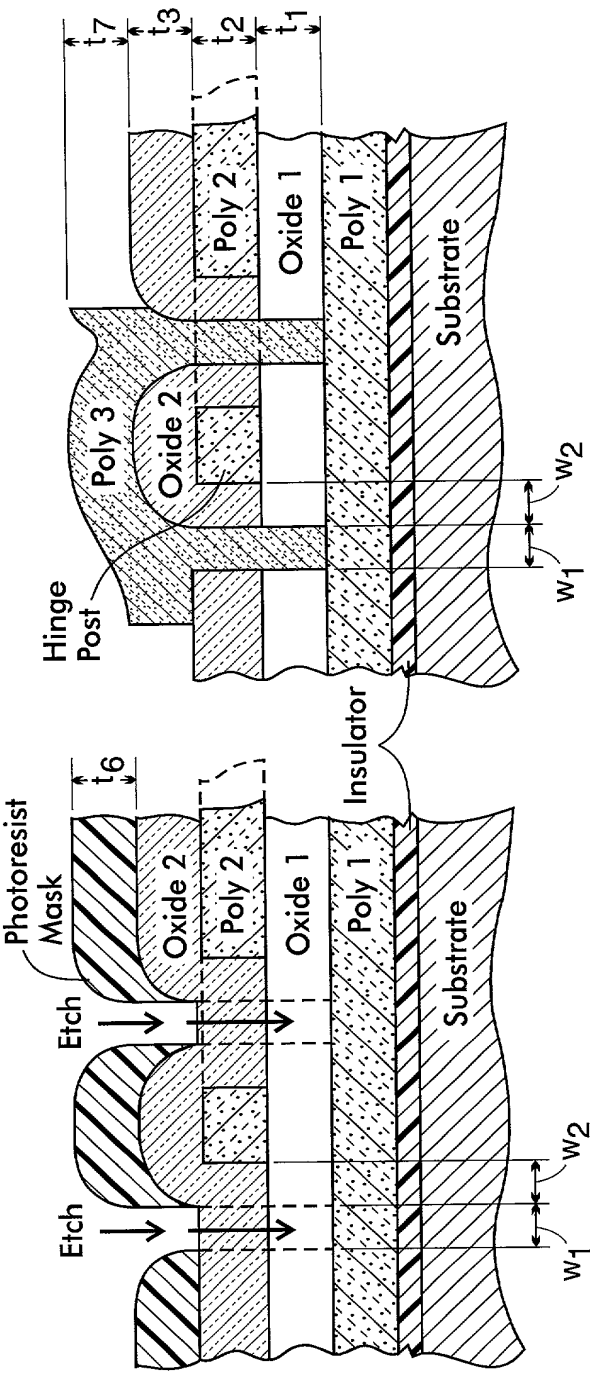


FIG. 18A



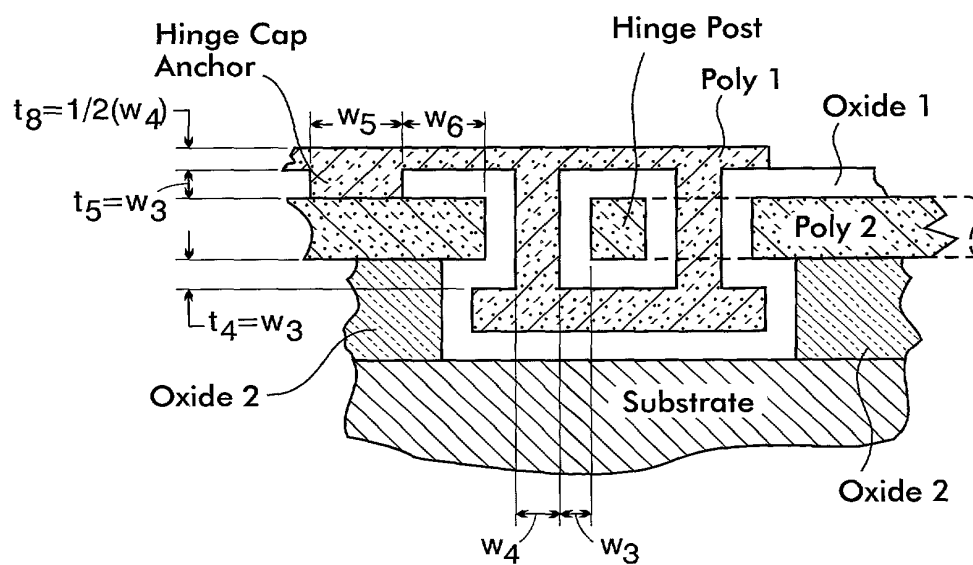


FIG. 18B

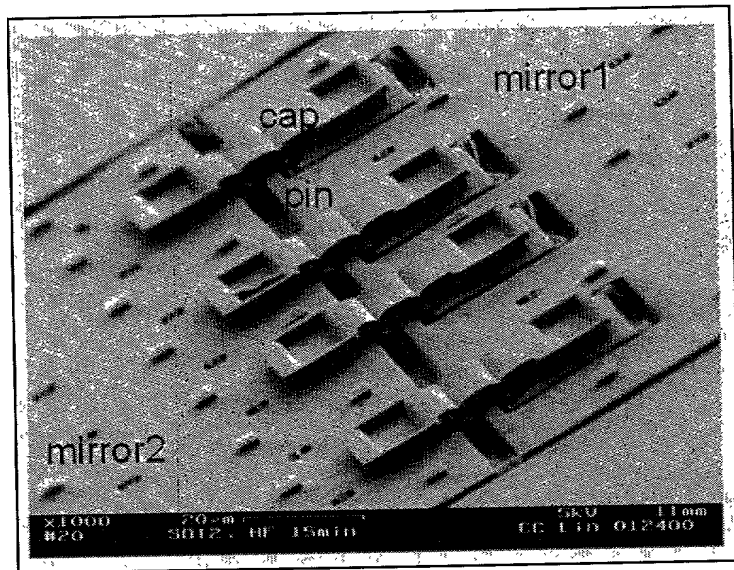


FIG. 19

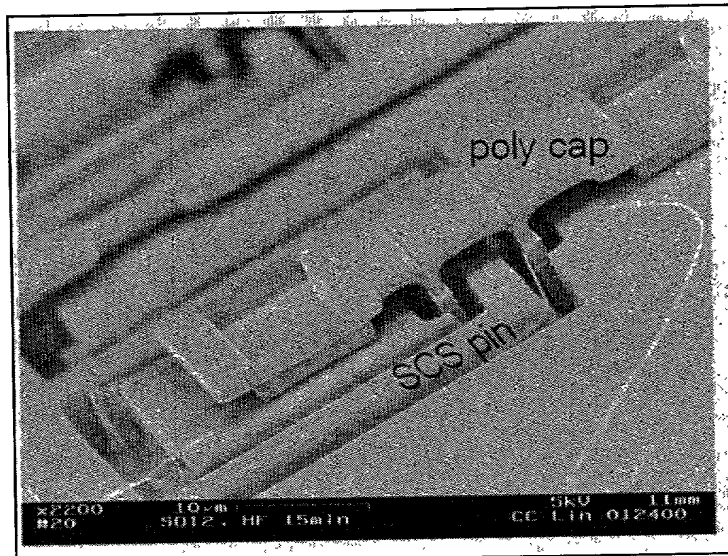


FIG. 20